

BLF7G22L-160; BLF7G22LS-160

Power LDMOS transistor

Rev. 2.1 — 2 November 2011

Product data sheet

1. Product profile

1.1 General description

160 W LDMOS power transistor for base station applications at frequencies from 2000 MHz to 2200 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25\text{ °C}$ in a common source class-AB production test circuit.

Mode of operation	f (MHz)	I_{Dq} (mA)	V_{DS} (V)	$P_{L(AV)}$ (W)	G_p (dB)	η_D (%)	ACPR (dBc)
2-carrier W-CDMA	2110 to 2170	1300	28	43	18.0	30	-32 ^[1]

[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R_{th} providing excellent thermal stability
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

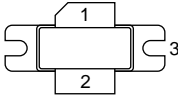
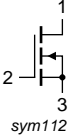
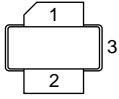
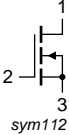
1.3 Applications

- RF power amplifiers for W-CDMA base stations and multi carrier applications in the 2000 MHz to 2200 MHz frequency range



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF7G22L-160 (SOT502A)			
1	drain		 sym112
2	gate		
3	source		
BLF7G22LS-160 (SOT502B)			
1	drain		 sym112
2	gate		
3	source		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF7G22L-160	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A
BLF7G22LS-160	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
I_D	drain current		-	36	A
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C}; P_L = 55\text{ W}$	0.29	K/W

6. Characteristics

Table 6. Characteristics

$T_j = 25\text{ }^\circ\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}$; $I_D = 2.16\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 216\text{ mA}$	1.5	1.9	2.3	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}$; $V_{DS} = 28\text{ V}$	-	-	4.5	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $V_{DS} = 10\text{ V}$	34	-	-	A
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	450	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}$; $I_D = 10.8\text{ A}$	-	20	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $I_D = 7.56\text{ A}$	-	0.06	-	Ω

7. Test information

Table 7. Application information

Mode of operation: 2-carrier W-CDMA; PAR 8.4 dB at 0.01 % probability on CCDF; 3GPP test model 1; 64 PDPCH; $f_1 = 2112.5\text{ MHz}$; $f_2 = 2117.5\text{ MHz}$; $f_3 = 2162.5\text{ MHz}$; $f_4 = 2167.5\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}$; $I_{Dq} = 1300\text{ mA}$; $T_{case} = 25\text{ }^\circ\text{C}$; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)} = 43\text{ W}$	16.5	18.0	-	dB
RL_{in}	input return loss	$P_{L(AV)} = 43\text{ W}$	-	-15	-6.5	dB
η_D	drain efficiency	$P_{L(AV)} = 43\text{ W}$	27	30	-	%
$ACPR_{5M}$	adjacent channel power ratio (5 MHz)	$P_{L(AV)} = 43\text{ W}$	-	-32	-28	dBc

Table 8. Application information

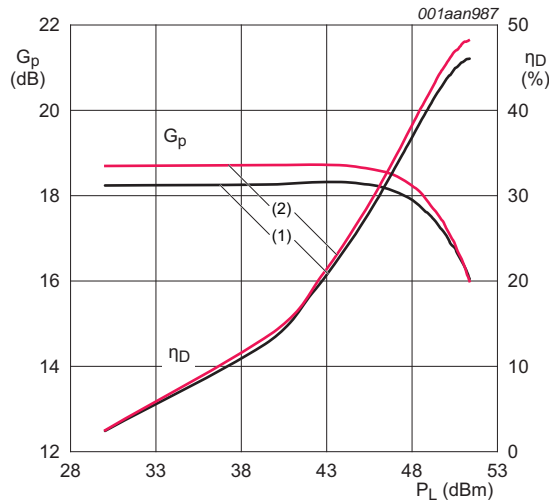
Mode of operation: 1-carrier W-CDMA; PAR 7.2 dB at 0.01 % probability on CCDF; 3GPP test model 1; 64 PDPCH; $f = 2167.5\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}$; $I_{Dq} = 1300\text{ mA}$; $T_{case} = 25\text{ }^\circ\text{C}$; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PAR_O	output peak-to-average ratio	$P_{L(AV)} = 100\text{ W}$; at 0.01 % probability on CCDF	3.9	4.15	-	dB

7.1 Ruggedness in class-AB operation

The BLF7G22L-160 and BLF7G22LS-160 are capable of withstanding a load mismatch corresponding to $V_{SWR} = 10 : 1$ through all phases under the following conditions: $V_{DS} = 28\text{ V}$; $I_{Dq} = 1300\text{ mA}$; $P_L = 160\text{ W}$; $f = 2110\text{ MHz}$.

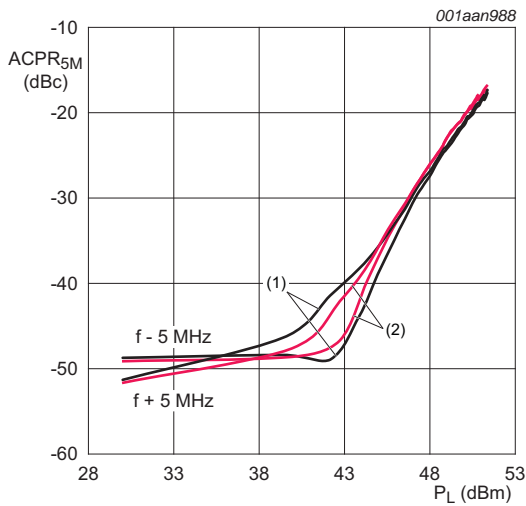
7.2 2-Carrier W-CDMA 5 MHz



$V_{DS} = 28$ V; $I_{Dq} = 1300$ mA.

- (1) $f = 2110$ MHz
- (2) $f = 2170$ MHz

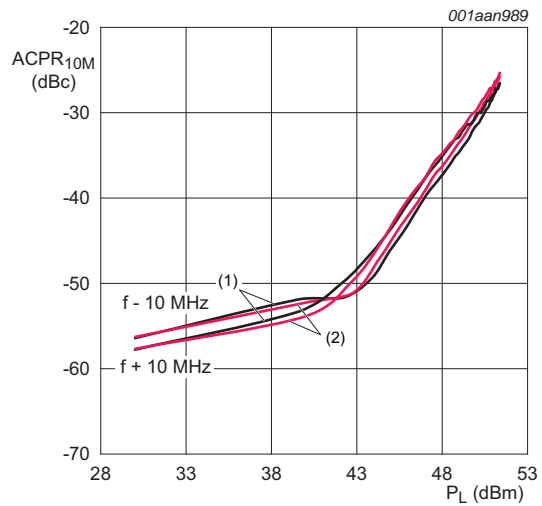
Fig 1. Power gain and drain efficiency as function of load power; typical values



$V_{DS} = 28$ V; $I_{Dq} = 1300$ mA.

- (1) $f = 2110$ MHz
- (2) $f = 2170$ MHz

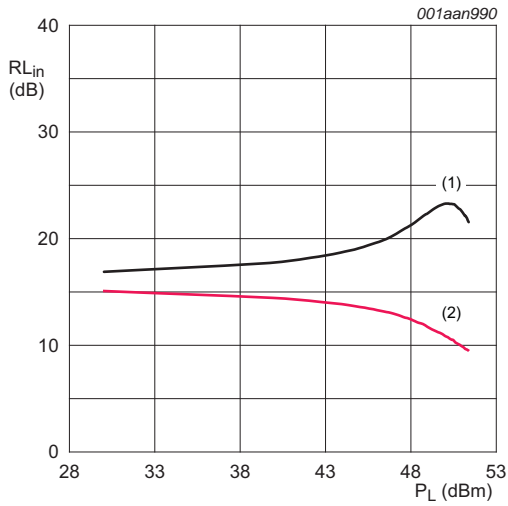
Fig 2. Adjacent channel power ratio (± 5 MHz) as a function of load power; typical values



$V_{DS} = 28$ V; $I_{Dq} = 1300$ mA.

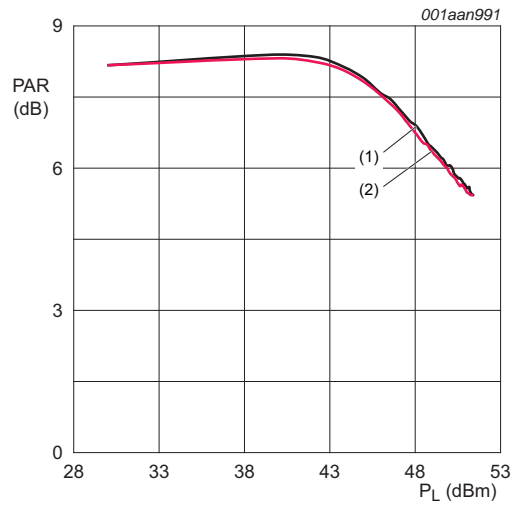
- (1) $f = 2110$ MHz
- (2) $f = 2170$ MHz

Fig 3. Adjacent channel power ratio (± 10 MHz) as a function of load power; typical values



$V_{DS} = 28\text{ V}; I_{Dq} = 1300\text{ mA}$.
 (1) $f = 2110\text{ MHz}$
 (2) $f = 2170\text{ MHz}$

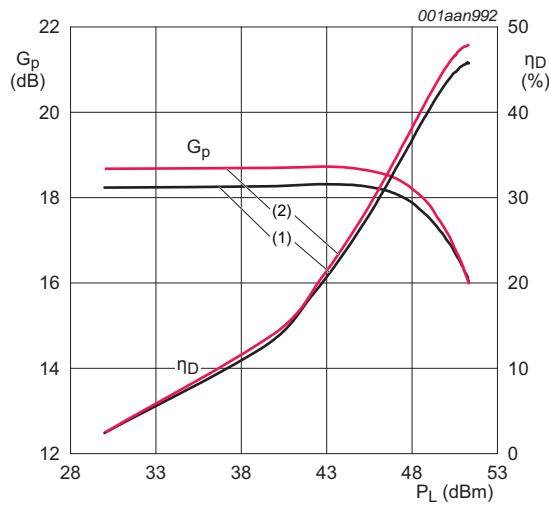
Fig 4. Input return loss as function of load power; typical values



$V_{DS} = 28\text{ V}; I_{Dq} = 1300\text{ mA}$.
 (1) $f = 2110\text{ MHz}$
 (2) $f = 2170\text{ MHz}$

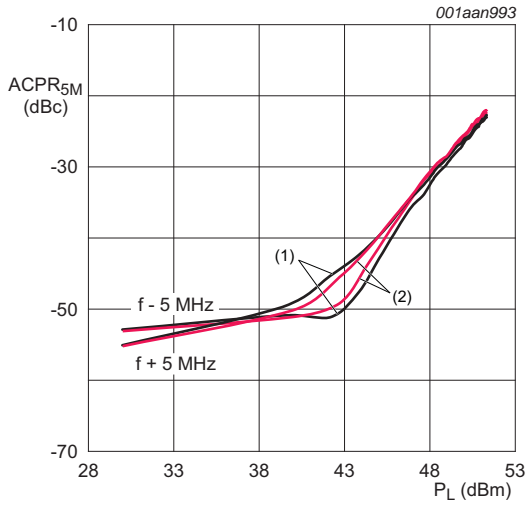
Fig 5. Peak-to-average power ratio as function of load power; typical values

7.3 2-Carrier W-CDMA 10 MHz



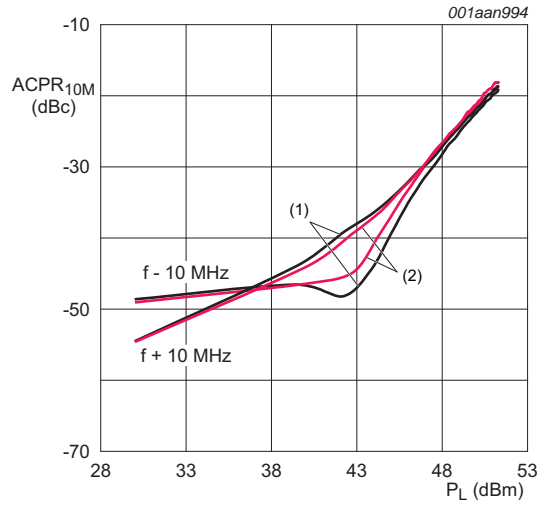
$V_{DS} = 28\text{ V}; I_{Dq} = 1300\text{ mA}$.
 (1) $f = 2110\text{ MHz}$
 (2) $f = 2170\text{ MHz}$

Fig 6. Power gain and drain efficiency as function of load power; typical values



$V_{DS} = 28\text{ V}; I_{Dq} = 1300\text{ mA}.$
 (1) $f = 2110\text{ MHz}$
 (2) $f = 2170\text{ MHz}$

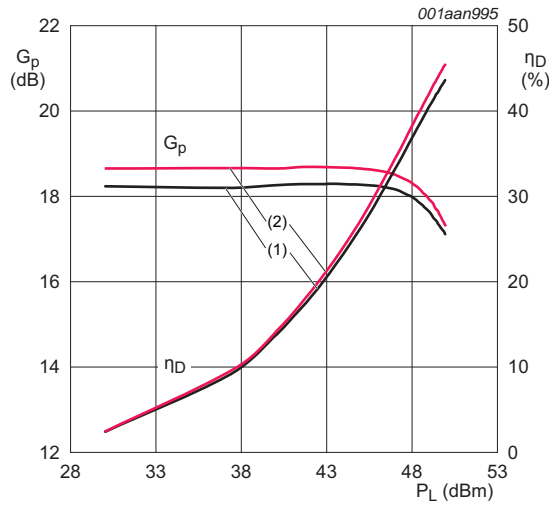
Fig 7. Adjacent channel power ratio ($\pm 5\text{ MHz}$) as a function of load power; typical values



$V_{DS} = 28\text{ V}; I_{Dq} = 1300\text{ mA}.$
 (1) $f = 2110\text{ MHz}$
 (2) $f = 2170\text{ MHz}$

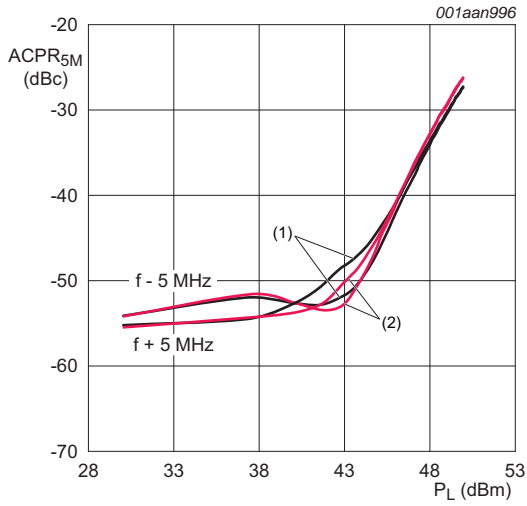
Fig 8. Adjacent channel power ratio ($\pm 10\text{ MHz}$) as a function of load power; typical values

7.4 1-Carrier W-CDMA



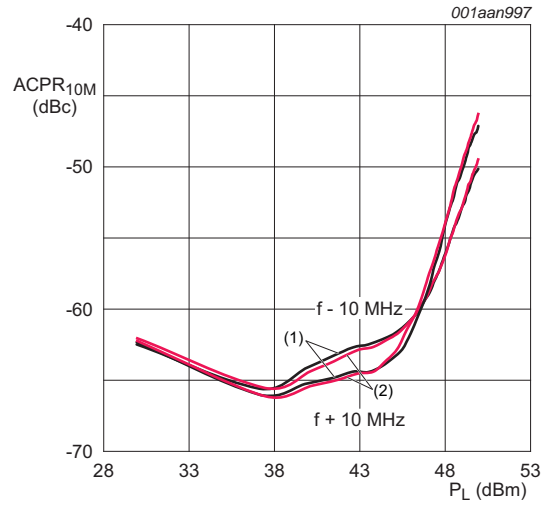
$V_{DS} = 28\text{ V}; I_{Dq} = 1300\text{ mA}.$
 (1) $f = 2110\text{ MHz}$
 (2) $f = 2170\text{ MHz}$

Fig 9. Power gain and drain efficiency as function of load power; typical values



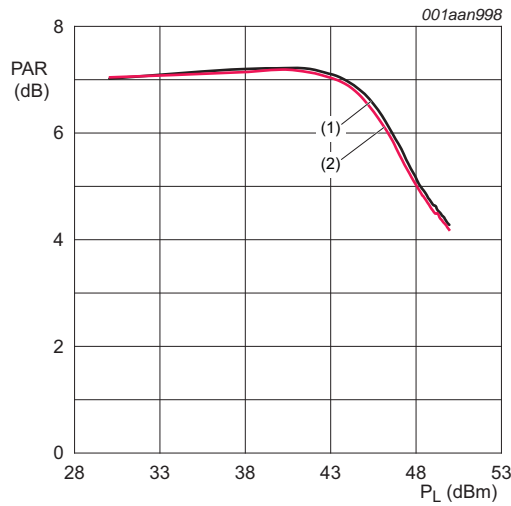
$V_{DS} = 28\text{ V}; I_{DQ} = 1300\text{ mA}$.
 (1) $f = 2110\text{ MHz}$
 (2) $f = 2170\text{ MHz}$

Fig 10. Adjacent channel power ratio ($\pm 5\text{ MHz}$) as a function of load power; typical values



$V_{DS} = 28\text{ V}; I_{DQ} = 1300\text{ mA}$.
 (1) $f = 2110\text{ MHz}$
 (2) $f = 2170\text{ MHz}$

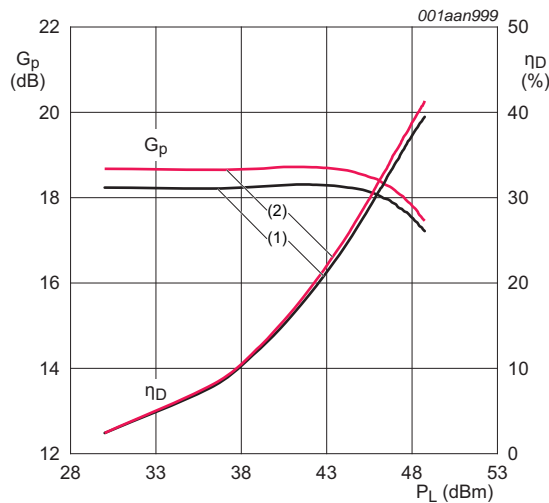
Fig 11. Adjacent channel power ratio ($\pm 10\text{ MHz}$) as a function of load power; typical values



$V_{DS} = 28\text{ V}; I_{DQ} = 1300\text{ mA}$.
 (1) $f = 2110\text{ MHz}$
 (2) $f = 2170\text{ MHz}$

Fig 12. Peak-to-average power ratio as function of load power; typical values

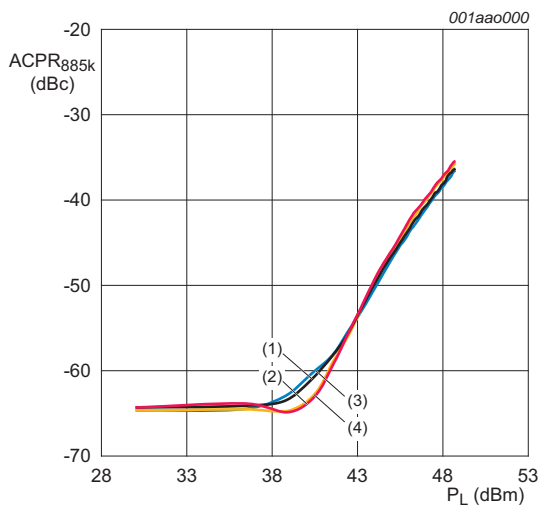
7.5 IS-95



$V_{DS} = 28\text{ V}; I_{Dq} = 1300\text{ mA}$.

- (1) $f = 2110\text{ MHz}$
- (2) $f = 2170\text{ MHz}$

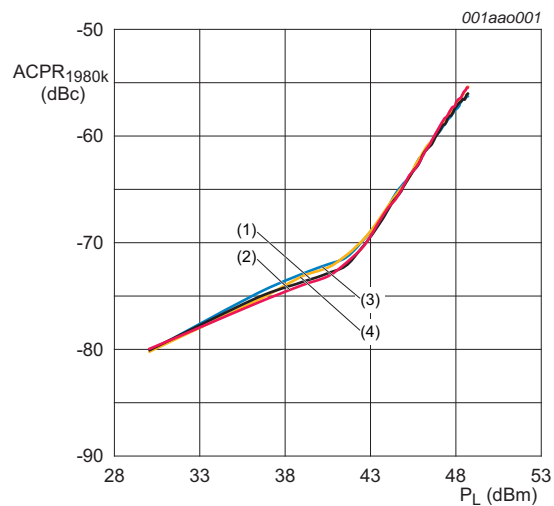
Fig 13. Power gain and drain efficiency as function of load power; typical values



$V_{DS} = 28\text{ V}; I_{Dq} = 1300\text{ mA}$.

- (1) $f = 2110\text{ MHz}; f + 885\text{ kHz}$
- (2) $f = 2170\text{ MHz}; f + 885\text{ kHz}$
- (3) $f = 2110\text{ MHz}; f - 885\text{ kHz}$
- (4) $f = 2170\text{ MHz}; f - 885\text{ kHz}$

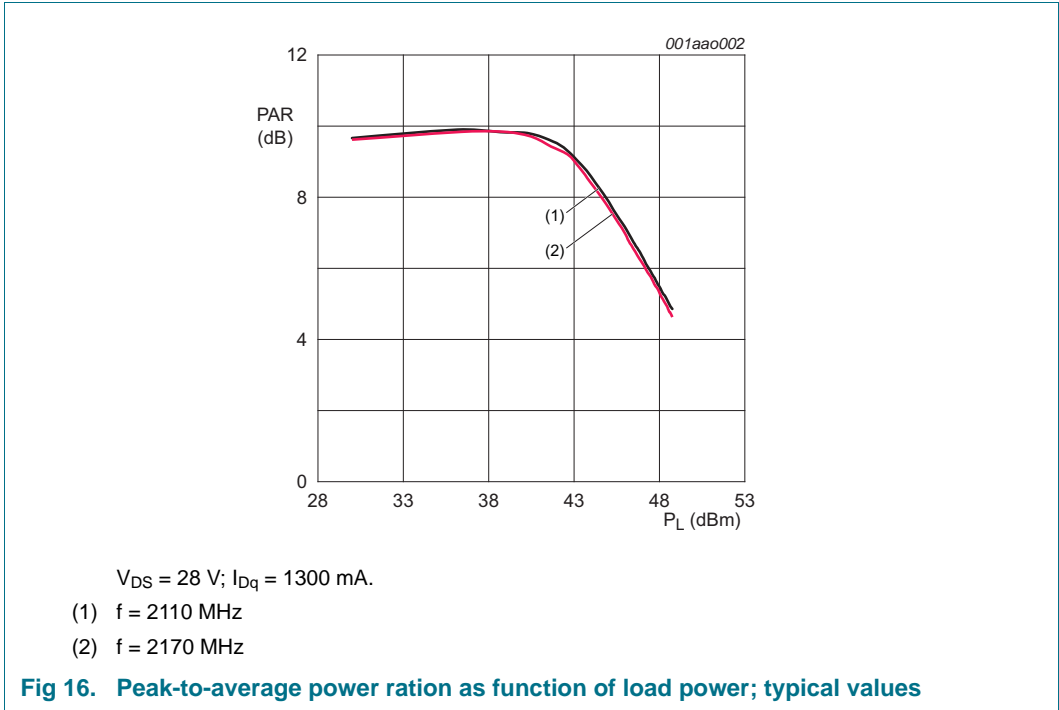
Fig 14. Adjacent channel power ratio ($\pm 5\text{ MHz}$) as a function of load power; typical values



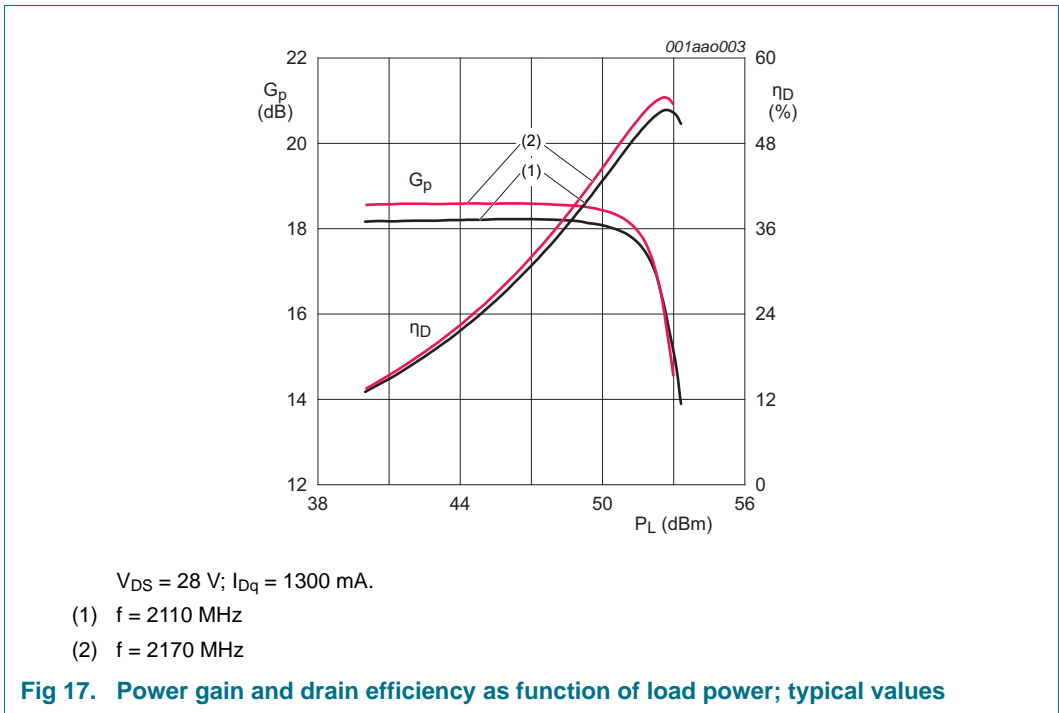
$V_{DS} = 28\text{ V}; I_{Dq} = 1300\text{ mA}$.

- (1) $f = 2110\text{ MHz}; f + 1980\text{ kHz}$
- (2) $f = 2170\text{ MHz}; f + 1980\text{ kHz}$
- (3) $f = 2110\text{ MHz}; f - 1980\text{ kHz}$
- (4) $f = 2170\text{ MHz}; f - 1980\text{ kHz}$

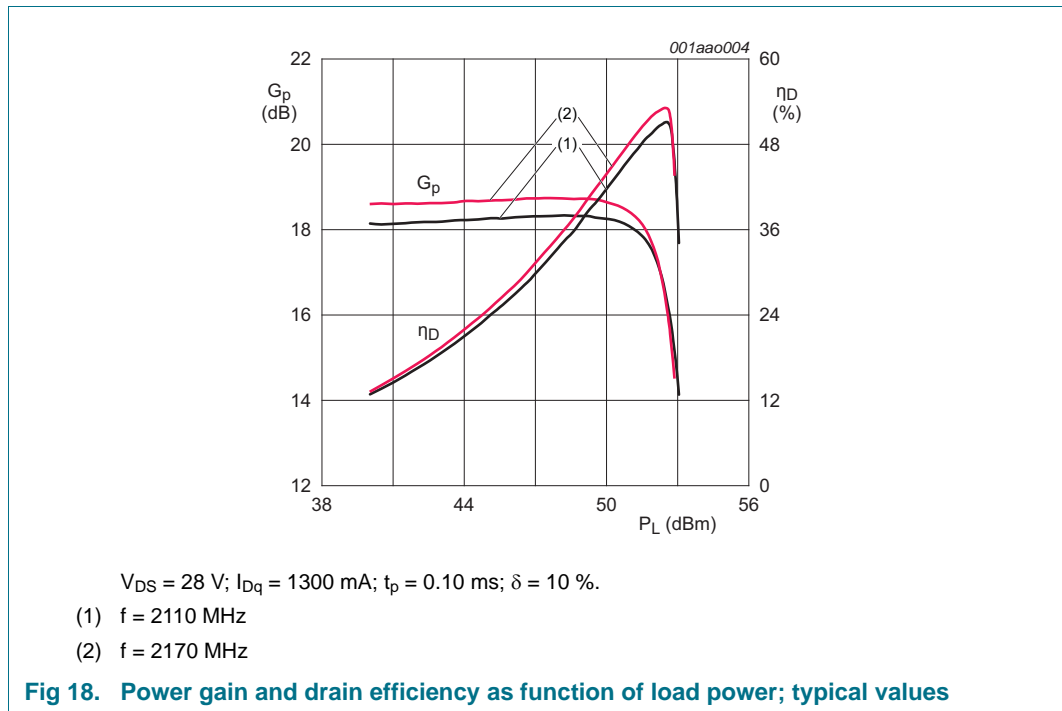
Fig 15. Adjacent channel power ratio ($\pm 10\text{ MHz}$) as a function of load power; typical values



7.6 CW



7.7 CW-pulsed



7.8 Test circuit

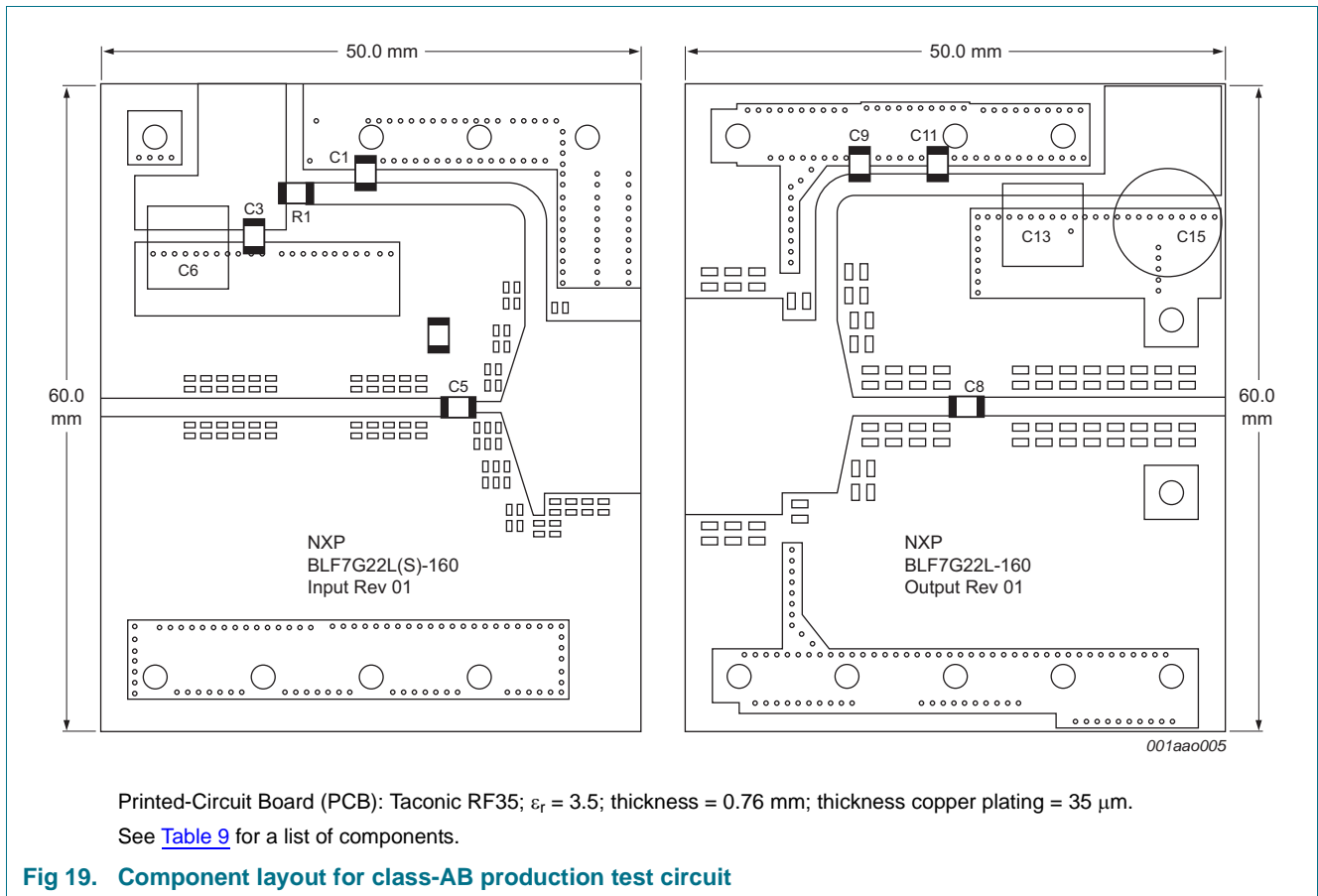


Table 9. List of components

For test circuit see [Figure 19](#).

Component	Description	Value	Remarks
C1, C5, C8, C9	multilayer ceramic chip capacitor	68 pF	[1]
C3, C11	multilayer ceramic chip capacitor	820 pF	[2]
C6, C13	multilayer ceramic chip capacitor	10 μF	[3]
C15	electrolytic capacitor	470 μF ; 63 V	
R1	SMD resistor	12 Ω	Philips 1206

[1] American Technical Ceramics type 800B or capacitor of same quality.

[2] American Technical Ceramics type 100A or capacitor of same quality.

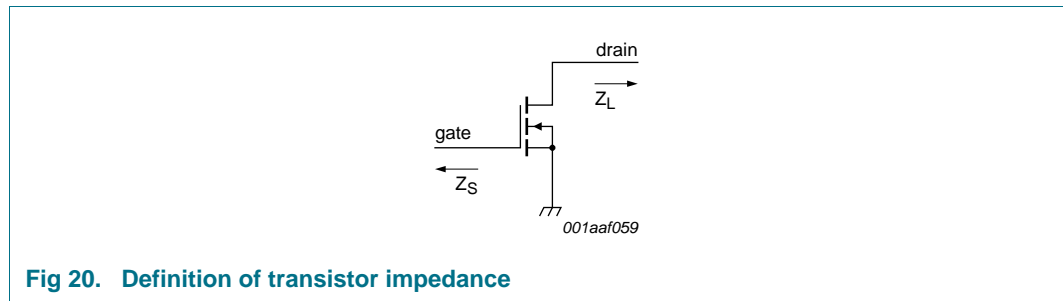
[3] TDK or capacitor of same quality.

7.9 Impedance information

Table 10. Typical impedance

Typical values unless otherwise specified.

f MHz	Z_S Ω	Z_L Ω
2050	1.39 – j4.13	1.41 – j3.80
2080	1.67 – j3.93	1.38 – j3.63
2110	2.01 – j3.89	1.35 – j3.45
2140	2.28 – j4.09	1.33 – j3.28
2170	2.27 – j4.47	1.31 – j3.12
2200	1.92 – j4.76	1.28 – j2.95
2230	1.42 – j4.75	1.26 – j2.79



8. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads

SOT502A

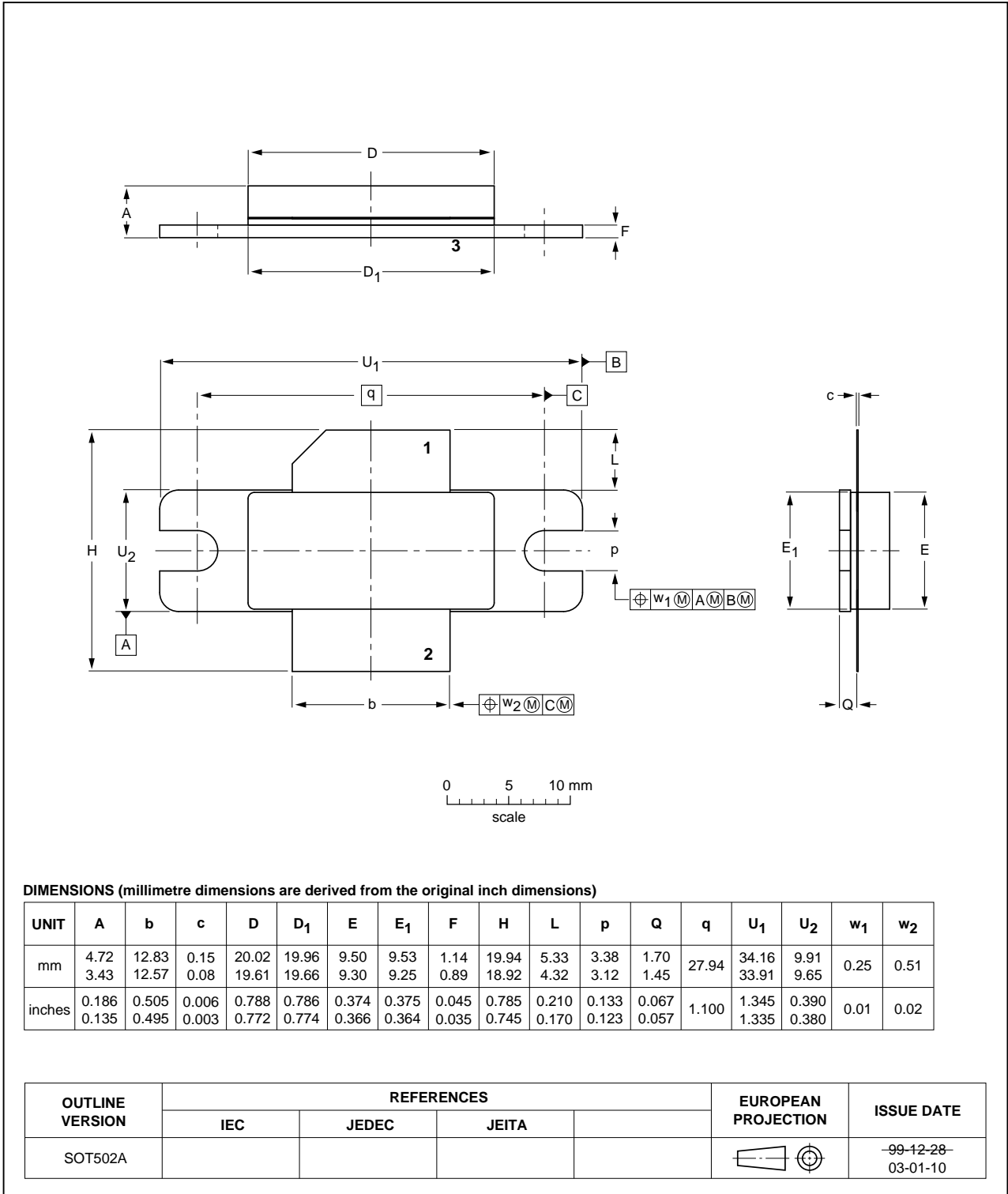


Fig 21. Package outline SOT502A

Earless flanged LDMOST ceramic package; 2 leads

SOT502B

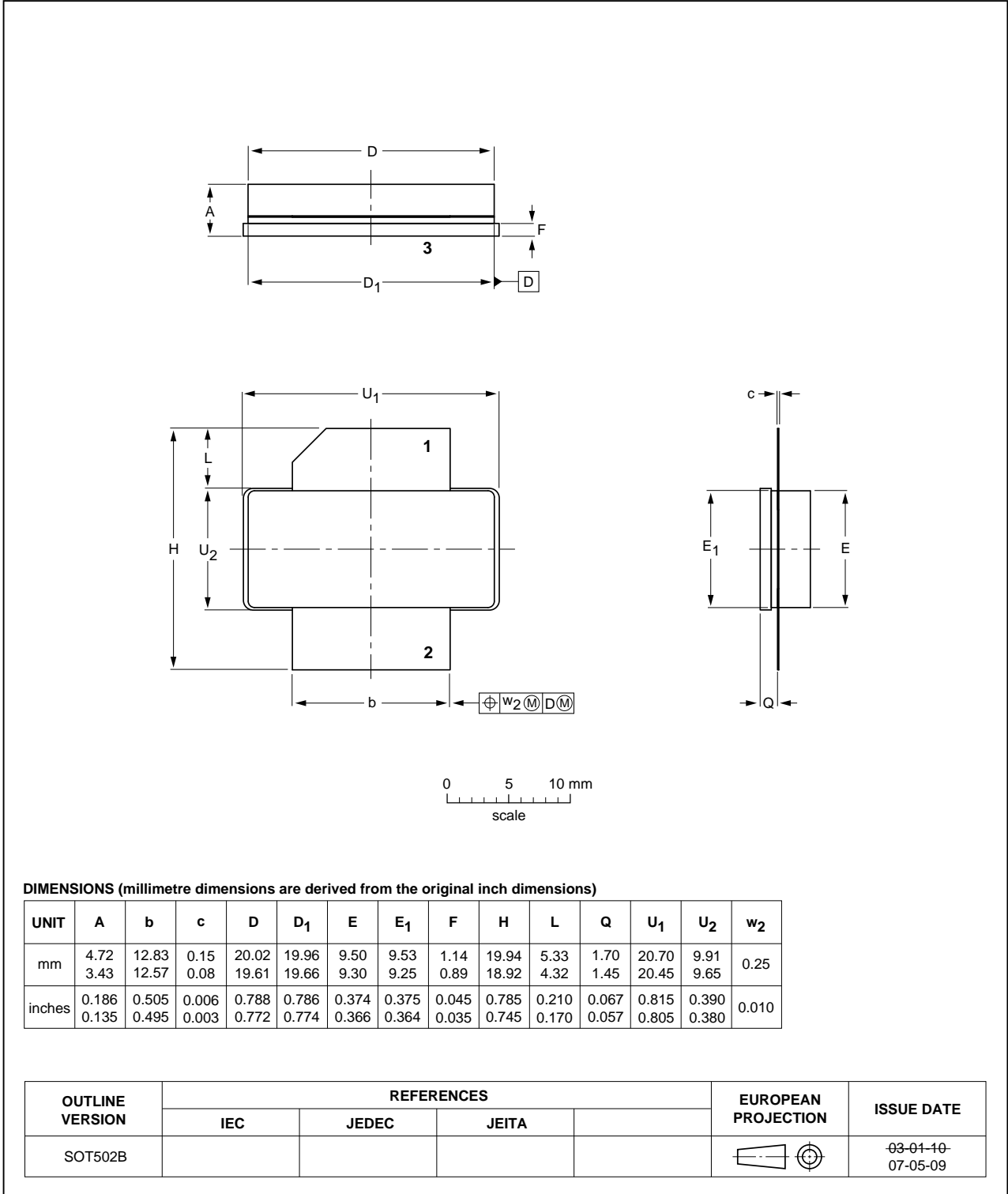


Fig 22. Package outline SOT502B

9. Abbreviations

Table 11. Abbreviations

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
PAR	Peak-to-Average power Ratio
PDPCH	transmission Power of the Dedicated Physical CHannel
RF	Radio Frequency
SMD	Surface Mounted Device
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

10. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF7G22L-160_7G22LS-160 v.2.1	20111102	Product data sheet	-	BLF7G22L-160_7G22LS-160 v.2
Modifications:	<ul style="list-style-type: none"> • Table 3: amended package descriptions 			
BLF7G22L-160_7G22LS-160 v.2	20111020	Product data sheet	-	BLF7G22L-160_7G22LS-160 v.1
Modifications:	<ul style="list-style-type: none"> • The status of this document has been changed to Product data sheet • Table 7 on page 3: the minimum value for η_D has been changed 			
BLF7G22L-160_7G22LS-160 v.1	20110427	Preliminary data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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